

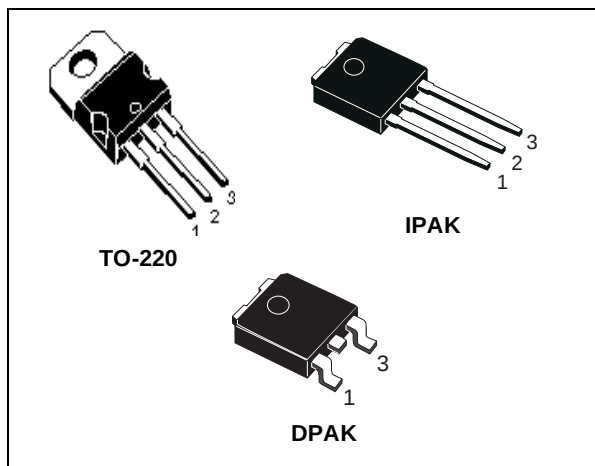


STP4NM60 STD3NM60 - STD3NM60-1

N-CHANNEL 600V - 1.3Ω - 3A TO-220/DPAK/IPAK
Zener-Protected MDmesh™ Power MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D	P _w
STP4NM60	600 V	< 1.5 Ω	4 A	69 W
STD3NM60	600 V	< 1.5 Ω	3 A	42 W
STD3NM60-1	600 V	< 1.5 Ω	3 A	42 W

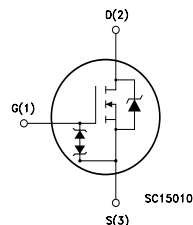
- TYPICAL R_{DS(on)} = 1.3 Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- IMPROVED ESD CAPABILITY
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL AND HIGH MANUFACTURING YIELDS



DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar completion's products.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

The MDmesh™ family is very suitable for increase the power density of high voltage converters allowing system miniaturization and higher efficiencies.

ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP4NM60	P4NM60	TO-220	TUBE
STD3NM60T4	D3NM60	DPAK	TAPE & REEL
STD3NM60-1	D3NM60	IPAK	TUBE

STP4NM60 / STD3NM60 / STD3NM60-1

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP4NM60	STD3NM60 STD3NM60-1	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	600		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	600		V
V _{GS}	Gate- source Voltage	± 30		V
I _D	Drain Current (continuous) at T _C = 25°C	4	3	A
I _D	Drain Current (continuous) at T _C = 100°C	2.52	1.9	A
I _{DM} (•)	Drain Current (pulsed)	16	12	A
P _{TOT}	Total Dissipation at T _C = 25°C	69	42	W
	Derating Factor	0.55	0.33	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	15		V/ns
T _j T _{stg}	Operating Junction Temperature Storage Temperature	-65 to 150 -65 to 150		°C °C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 3A, di/dt ≤ 400 μA, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

THERMAL DATA

		TO-220	DPAK IPAK	
R _{thj-case}	Thermal Resistance Junction-case Max	1.82	3	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	1.5	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	200	mJ

GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{GSO}	Gate-Source Breakdown Voltage	I _{gs} = ± 1mA (Open Drain)	30			V

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}C$ UNLESS OTHERWISE SPECIFIED)
ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0$	600			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}, T_C = 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 5	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V, I_D = 1.5 A$		1.3	1.5	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (1)$	Forward Transconductance	$V_{DS} = 15 V, I_D = 1.5 A$		2.7		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		324 132 7.4		pF pF pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 300 V, I_D = 1.5 A$ $R_G = 4.7 \Omega, V_{GS} = 10 V$ (Resistive Load see, Figure 3)		9 4		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 480V, I_D = 3 A,$ $V_{GS} = 10V$		10 3 4.7	14	nC nC nC

SWITCHING OFF

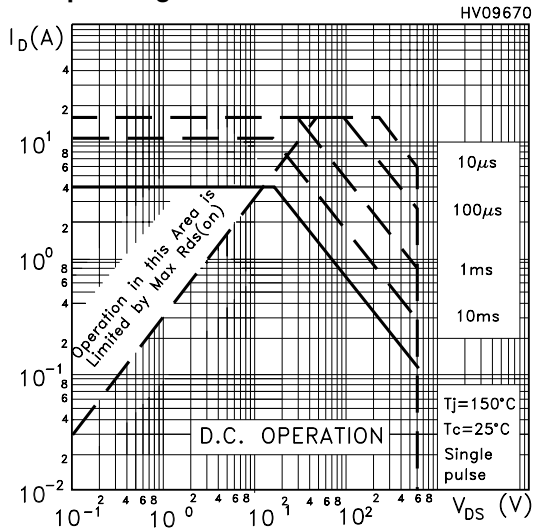
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 480 V, I_D = 3 A,$ $R_G = 4.7 \Omega, V_{GS} = 10V$ (Inductive Load see, Figure 5)		16.5 10.5 15		ns ns ns

SOURCE DRAIN DIODE

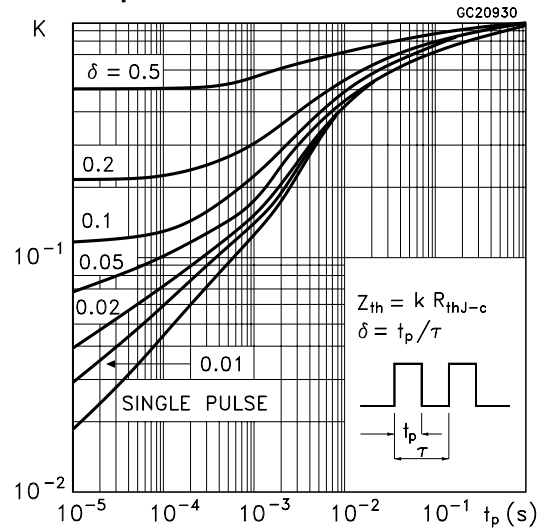
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (2)$	Source-drain Current Source-drain Current (pulsed)				3 12	A A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 3 A, V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 3 A, di/dt = 100A/\mu s$ $V_{DD} = 100 V, T_j = 25^{\circ}C$ (see test circuit, Figure 5)		224 1 9		ns μC A
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 3 A, di/dt = 100A/\mu s$ $V_{DD} = 100 V, T_j = 150^{\circ}C$ (see test circuit, Figure 5)		296 1.4 9.3		ns μC A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

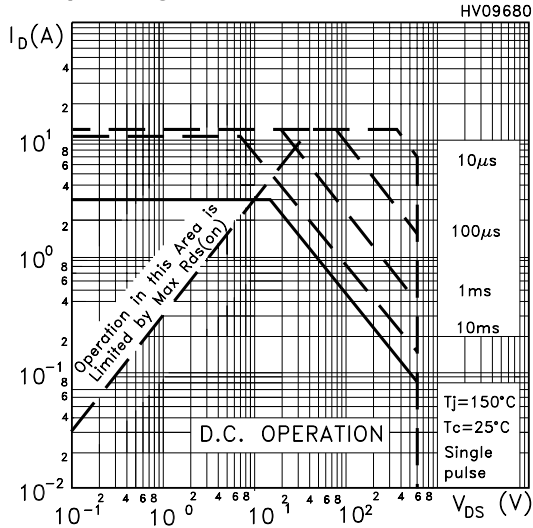
Safe Operating Area For TO-220



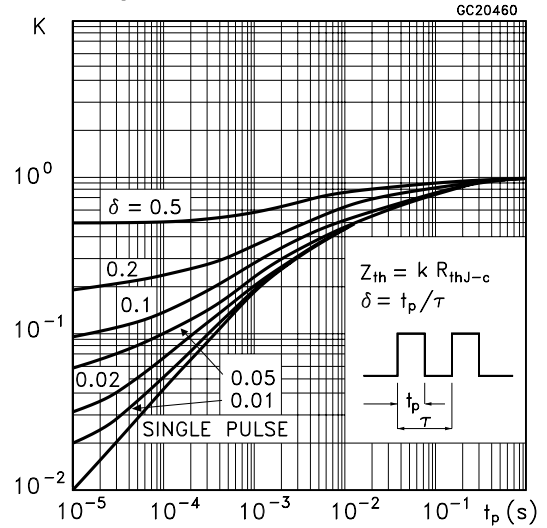
Thermal Impedance For TO-220



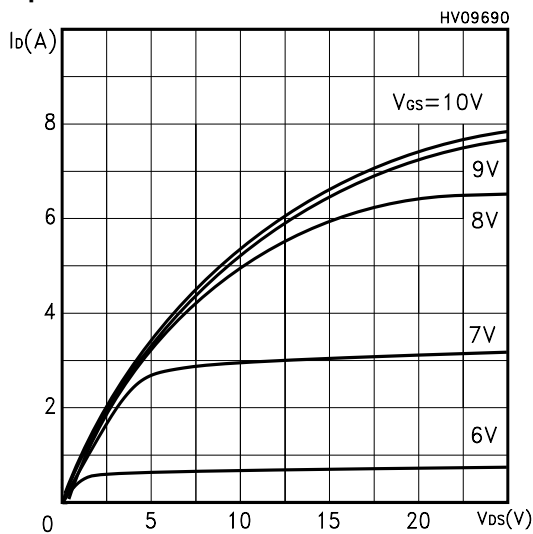
Safe Operating Area For DPAK / IPAK



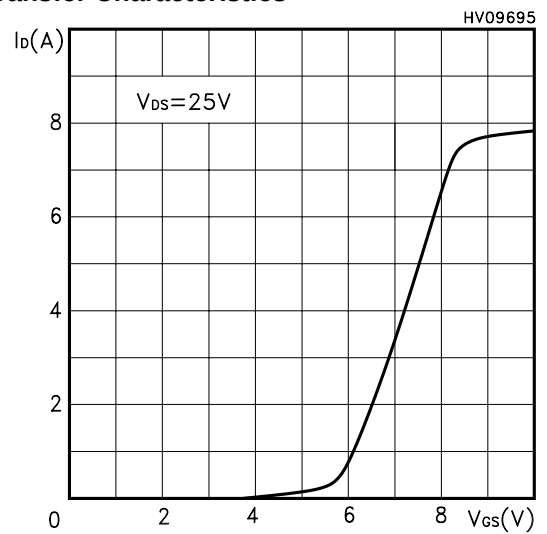
Thermal Impedance For DPAK / IPAK



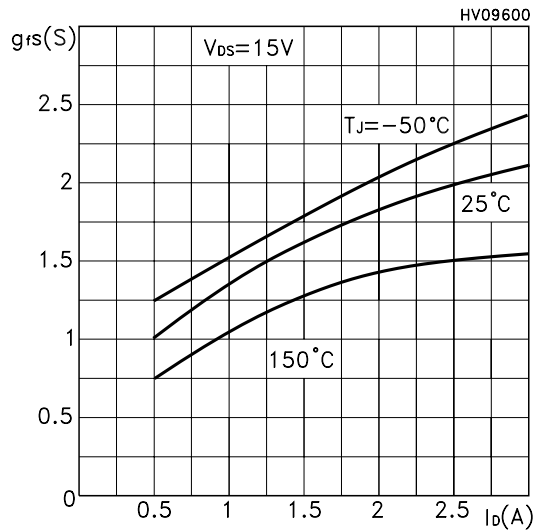
Output Characteristics



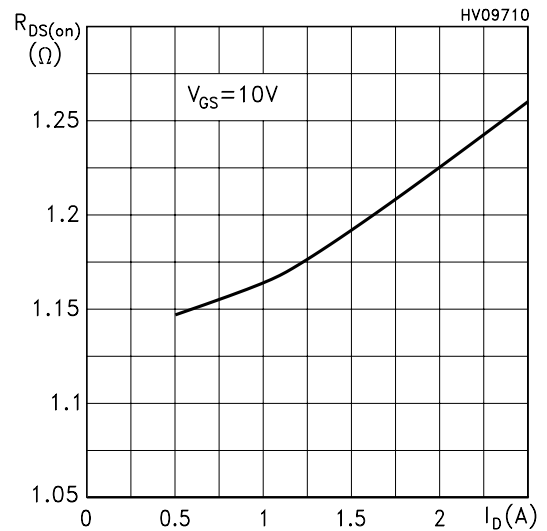
Transfer Characteristics



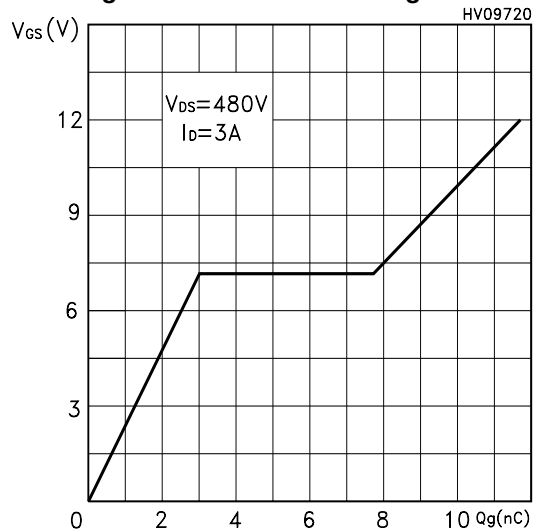
Transconductance



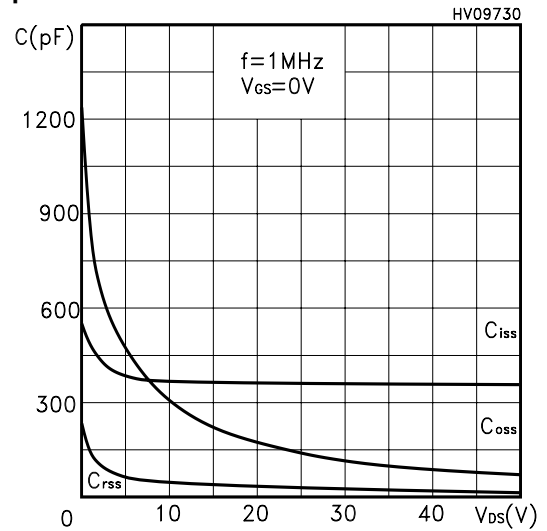
Static Drain-source On Resistance



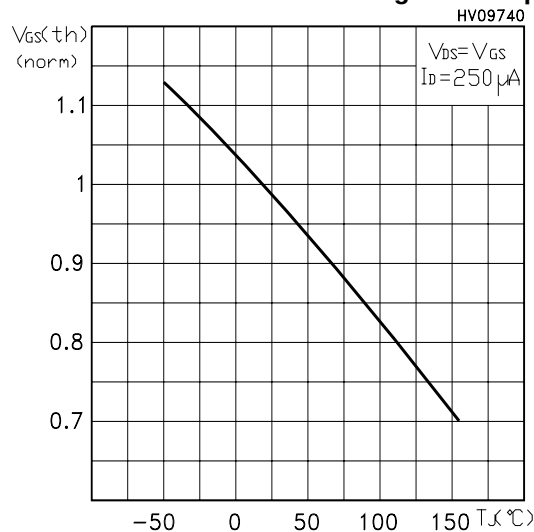
Gate Charge vs Gate-source Voltage



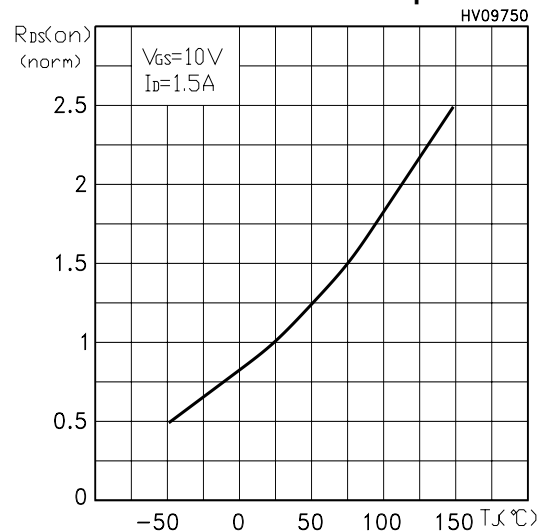
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

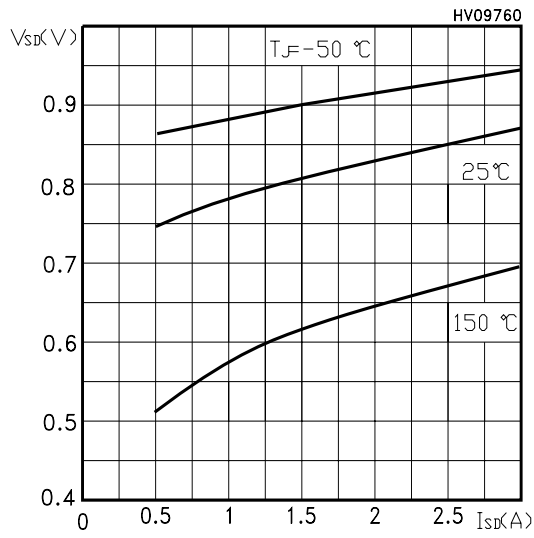


Fig. 1: Unclamped Inductive Load Test Circuit

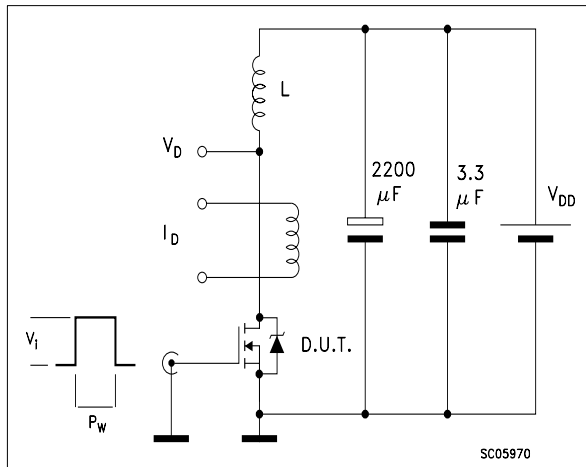


Fig. 2: Unclamped Inductive Waveform

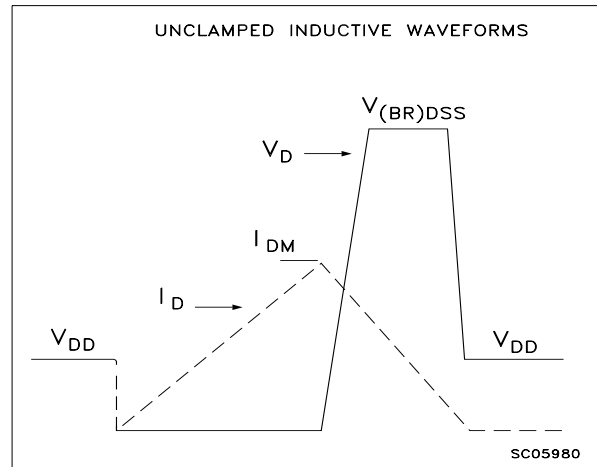


Fig. 3: Switching Times Test Circuit For Resistive Load

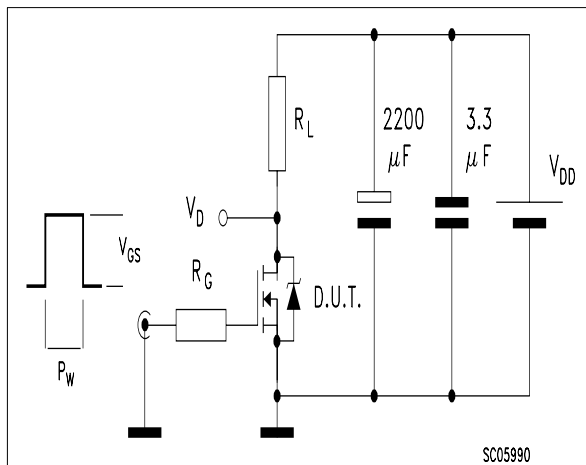


Fig. 4: Gate Charge test Circuit

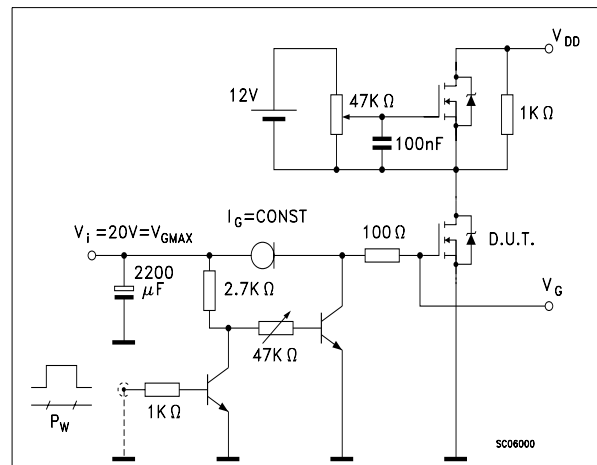
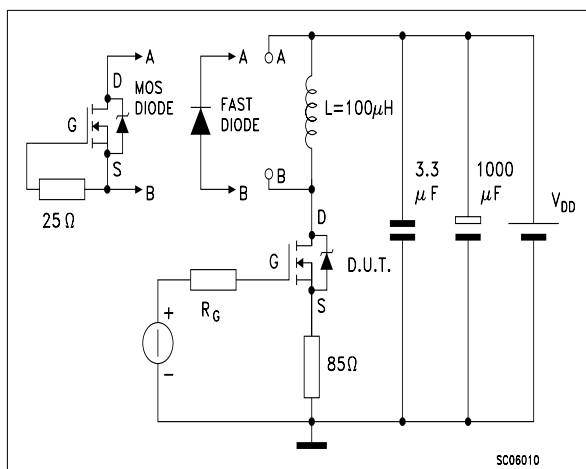
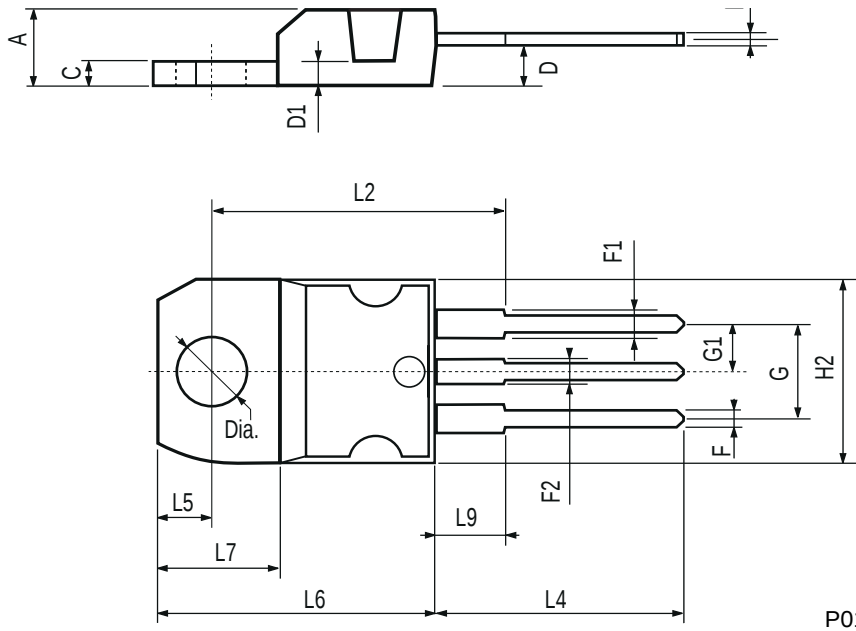


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

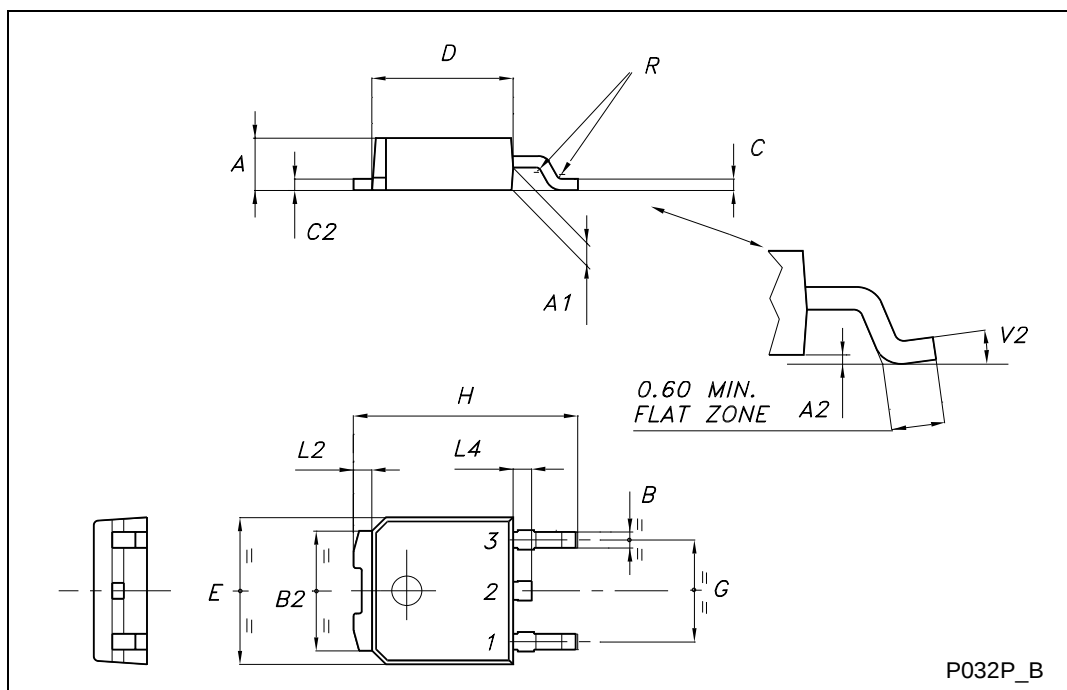
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



P011C

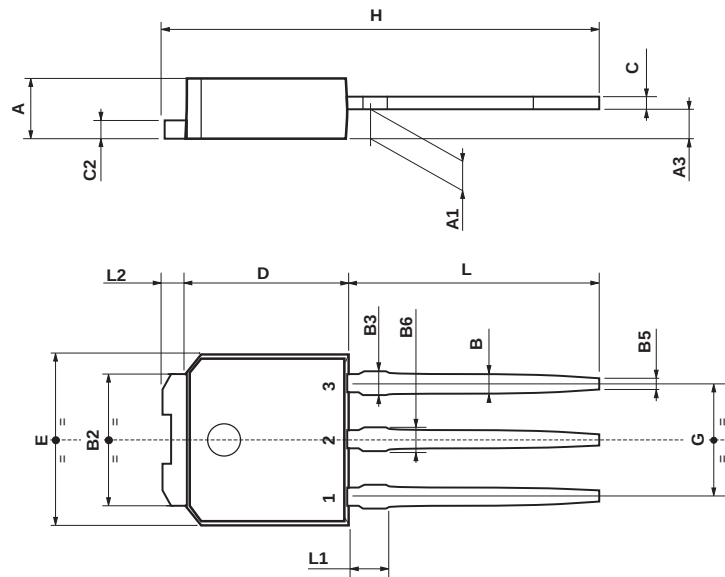
TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°

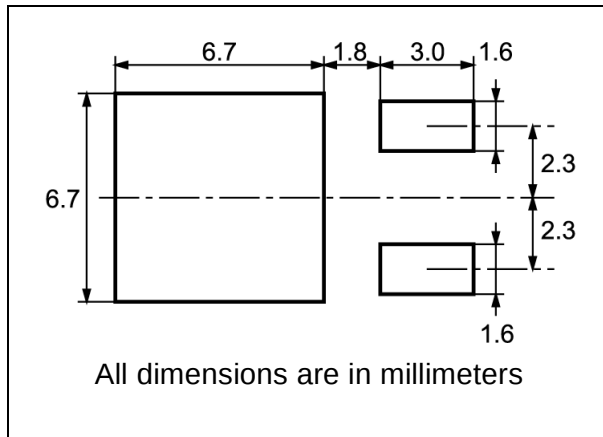
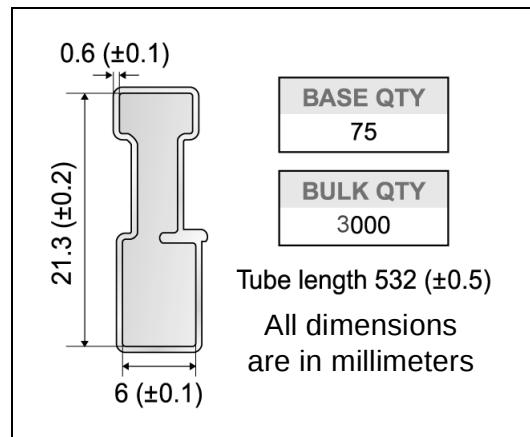
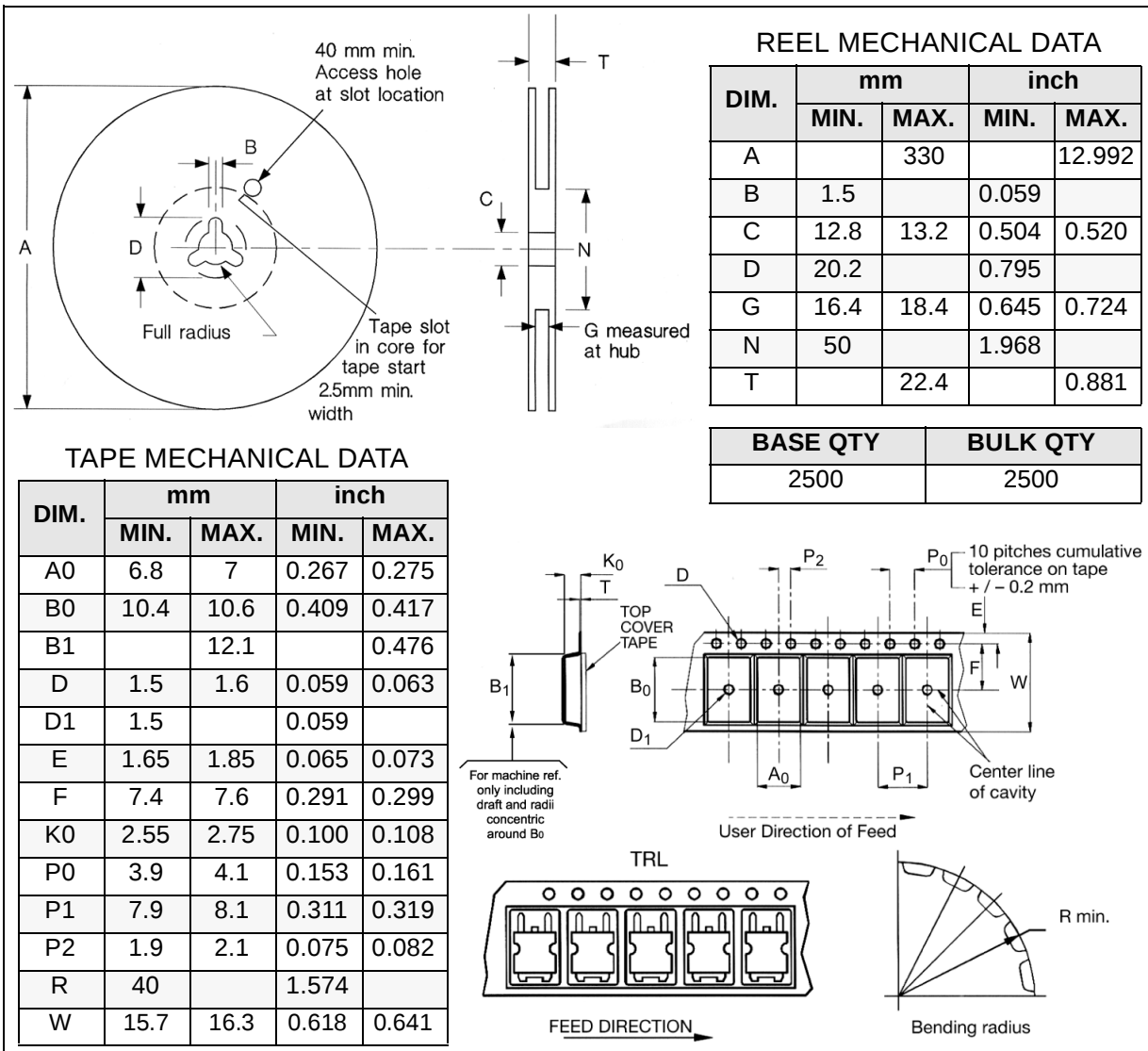


TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



0068771-E

DPAK FOOTPRINT**TUBE SHIPMENT (no suffix)*****TAPE AND REEL SHIPMENT (suffix "T4")***

* on sales type



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